

DESCRIPTION

The MX3004 uses advanced trench technology to provide excellent $R_{DS(ON)}$ and low gate charge. It can be used in a wide variety of applications.

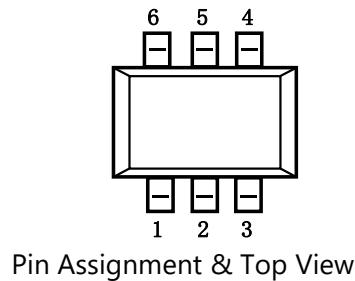
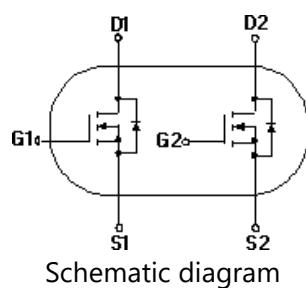
GENERAL FEATURES

- $V_{DS}=30V$, $I_D=4.4A$
 $R_{DS(ON)}(\text{Typ.})=37m\Omega$ @ $V_{GS}=4.5V$
 $R_{DS(ON)}(\text{Typ.})=23m\Omega$ @ $V_{GS}=10V$
- Surface-mounted package
- Advanced trench cell design

APPLICATION

- Portable appliances
- Battery management
- High speed switch
- Low power DC-DC Converter

PINOUT



Pin	Description
1	Gate(G1)
2	Source(S2)
3	Gate(G2)
4	Drain(D2)
5	Source(S1)
6	Drain(D1)

ORDERING INFORMATION

Part Number	Storage Temperature	Package	Devices Per Reel
MX3004	-55°C to 150°C	SOT23-6	3000

ABSOLUTE MAXIMUM RATINGS ($T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous($V_{GS}=10V$) ^(Note1)	I_D	4.4	A
Drain Current-Continuous($V_{GS}=10V, T_A=100^\circ C$) ^(Note1)	I_D	2.8	A
Pulsed Drain Current($V_{GS}=10V$) ^{(Note1)(Note2)}	I_{DM}	17.6	A
Drain Power Dissipation	P_{tot}	0.83	W
Continuous-Source Current ^(Note1)	I_S	4.4	A
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	°C

THERMAL RESISTANCE

Thermal Resistance, Junction-to-Ambient ^(Note1)	$R_{\theta JA}$	150	°C/W
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Note 1. Surface Mounted on 1 in² pad area, $t \leq 10$ sec

Note 2. Pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$

Note 3. limited by bonding wire


ELECTRICAL CHARACTERISTICS($T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
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Off Characteristics

Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	30	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=24V, V_{GS}=0V$	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 100	nA

On Characteristics

Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1	-	2	V
Drain-Source On-State Resistance ^(Note1)	$R_{DS(ON)}$	$V_{GS}=4.5V, I_D=2A$	-	37	45	$m\Omega$
		$V_{GS}=10V, I_D=3A$	-	23	27	$m\Omega$

Dynamic Characteristics^(Note2)

Input Capacitance	C_{iss}	$V_{DS}=15V, V_{GS}=0V, F=1.0MHz$	-	363	-	pF
Output Capacitance	C_{oss}		-	49	-	pF
Reverse Transfer Capacitance	C_{rss}		-	39	-	pF

Switching Characteristics^(Note2)

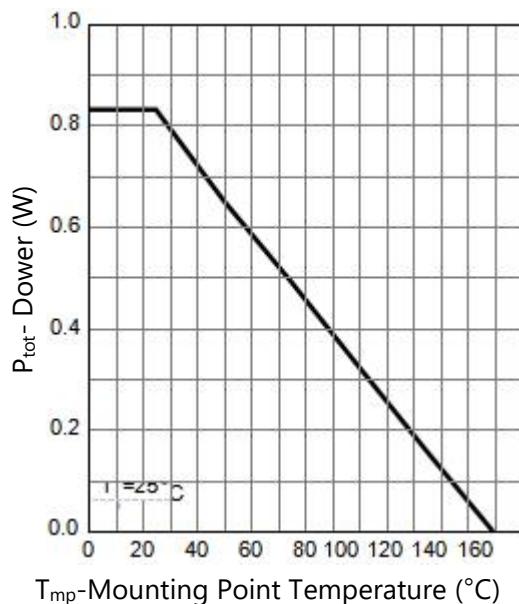
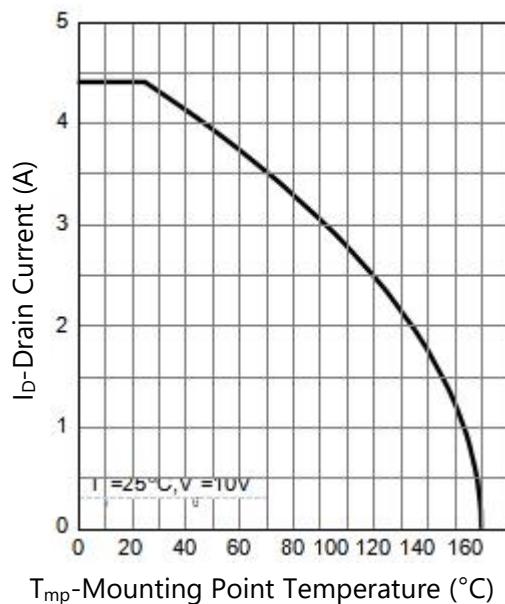
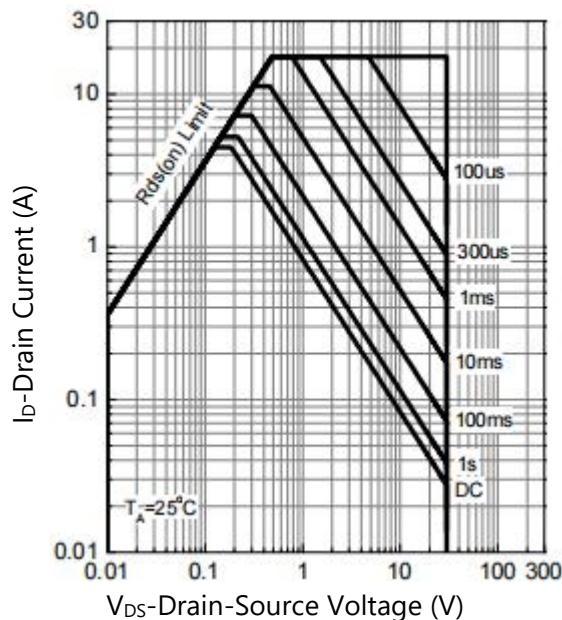
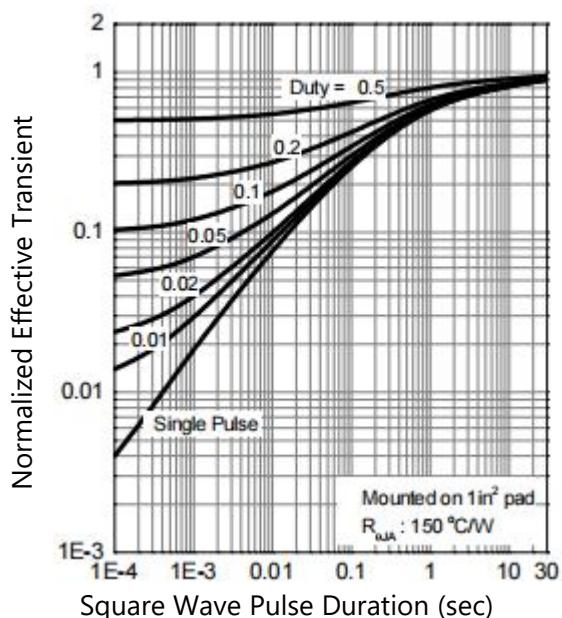
Turn-on Delay Time	$t_{d(on)}$	$V_{DS}=15V, R_L=5\Omega$ $V_{GEN}=10V, R_G=3.9\Omega$ $I_{DS}=3A$	-	3.9	-	nS
Turn-on Rise Time	t_r		-	8.8	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	10	-	nS
Turn-Off Fall Time	t_f		-	3.7	-	nS
Total Gate Charge	Q_g	$V_{DS}=15V, I_{DS}=3A,$ $V_{GS}=10V$	-	7.2	-	nC
Gate-Source Charge	Q_{gs}		-	1.7	-	nC
Gate-Drain Charge	Q_{gd}		-	1	-	nC

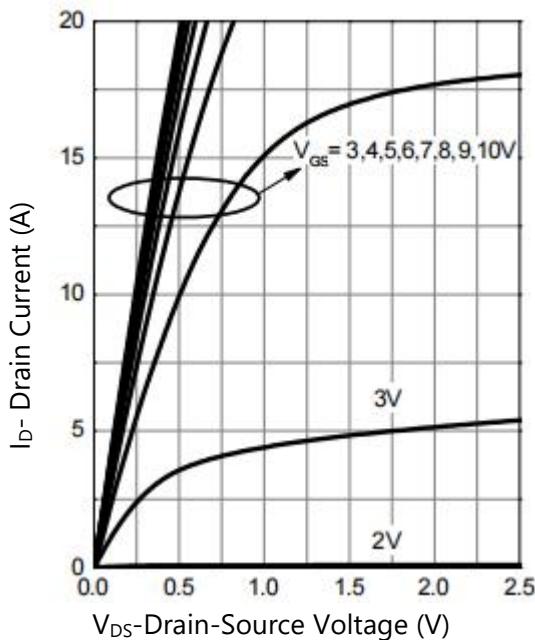
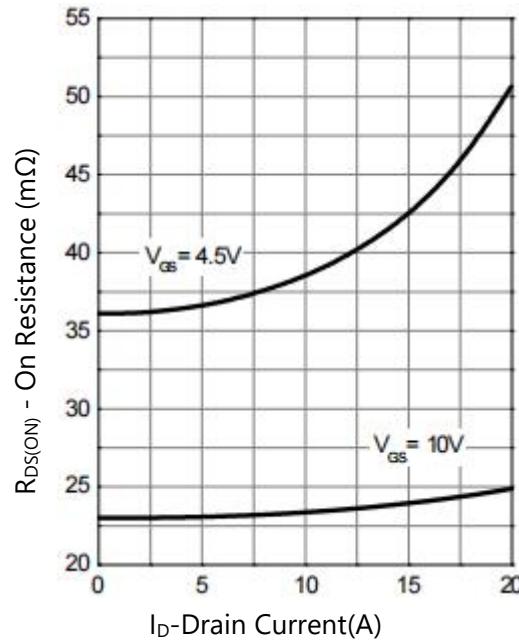
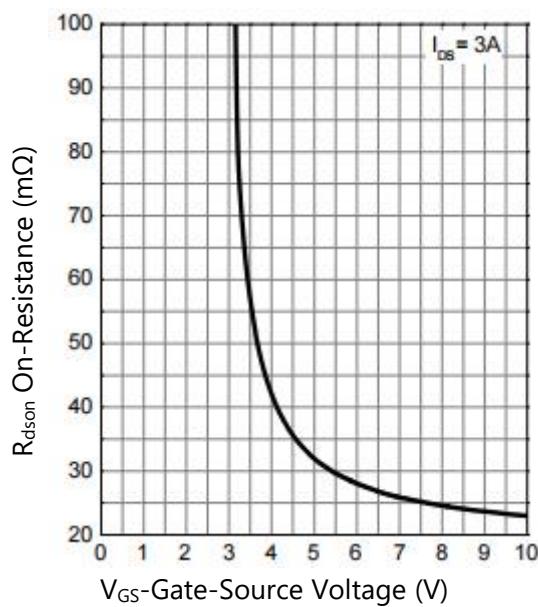
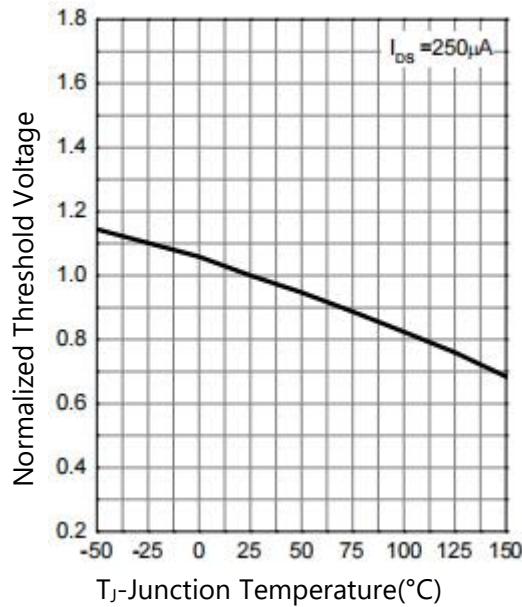
Drain-Source Diode Characteristics

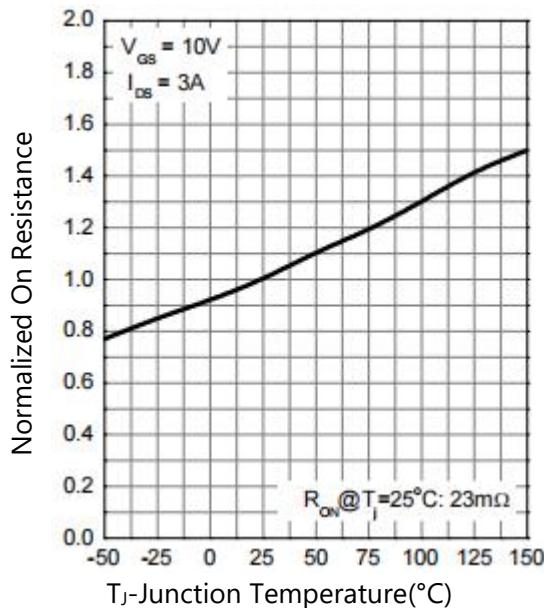
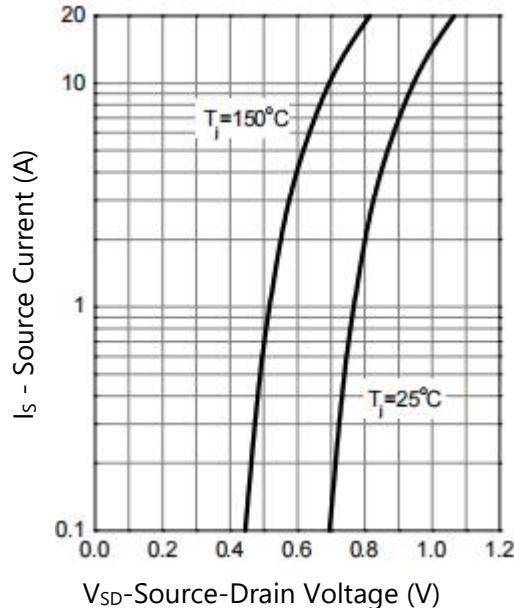
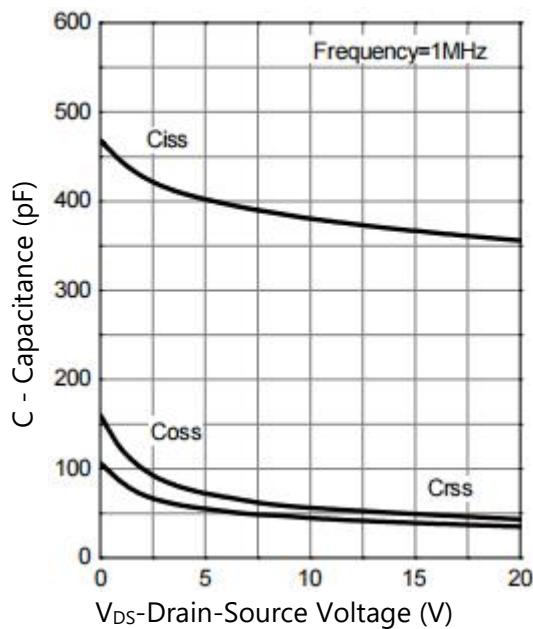
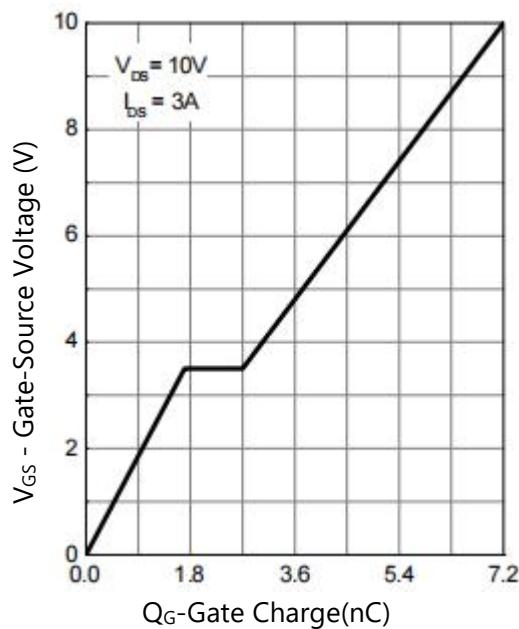
Diode Forward Voltage ^(Note 1)	V_{SD}	$V_{GS}=0V, I_{SD}=3A$	-	-	1.3	V
Reverse Recovery Time	t_{rr}	$I_{DS}=3A$ $dI_{SD}/dt=100A/\mu s$	-	5.9	-	ns
Reverse Recovery Charge	Q_{rr}		-	2.4	-	nc

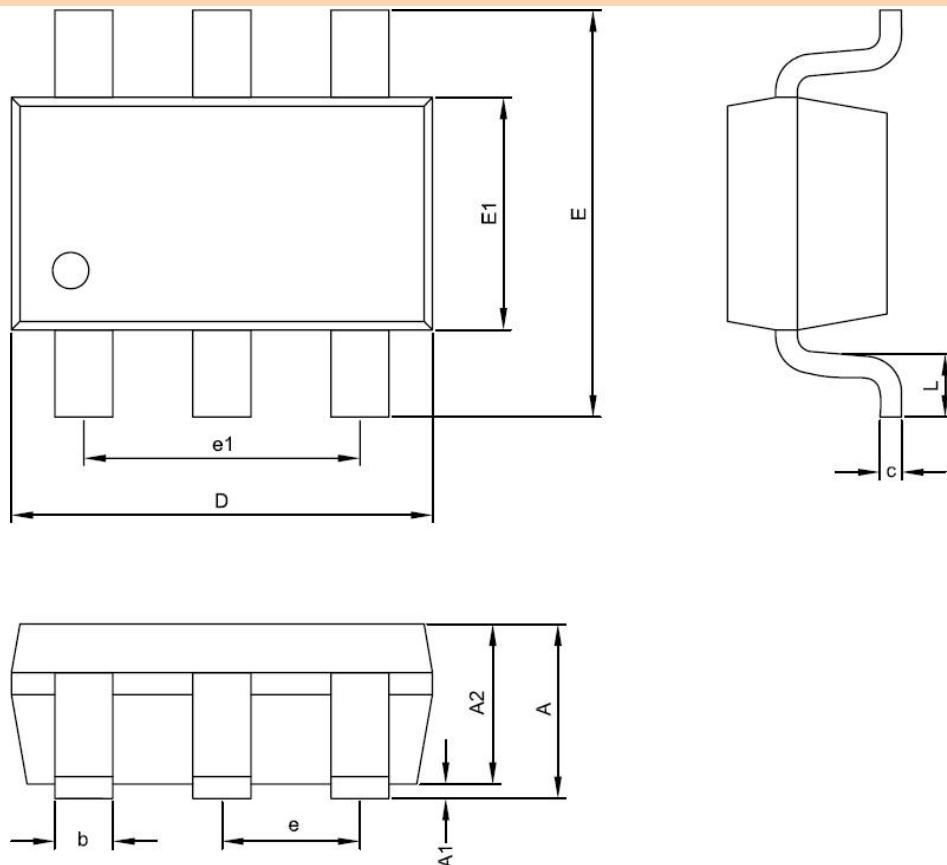
Note 1. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.

Note 2. Guaranteed by design, not subject to product.


TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS
Figure 1. Power Capability

Figure 2. Current Capability

Figure 3. Safe Operating Area

Figure 4. Transient Thermal Impedance



TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS
Figure 5. Output Characteristics

Figure 6. On Resistance

Figure 7. Transfer Characteristics

Figure 8. Normalized Threshold Voltage



TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS
Figure 9. Normalized On Resistance

Figure 10. Diode Forward Current

Figure 11. Capacitance

Figure 12. Gate Charge


PACKAGE INFORMATION
SOT23-6L


Symbol	Dimensions In Millimeters	
	Min.	Max.
A	-	1.45
A1	-	0.15
A2	0.90	1.30
D	2.90 BSC	
E	2.80 BSC	
E1	1.50	1.70
c	0.08	0.25
b	0.30	0.50
e	0.95 BSC	
e1	1.90 BSC	
L	0.30	0.60